Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

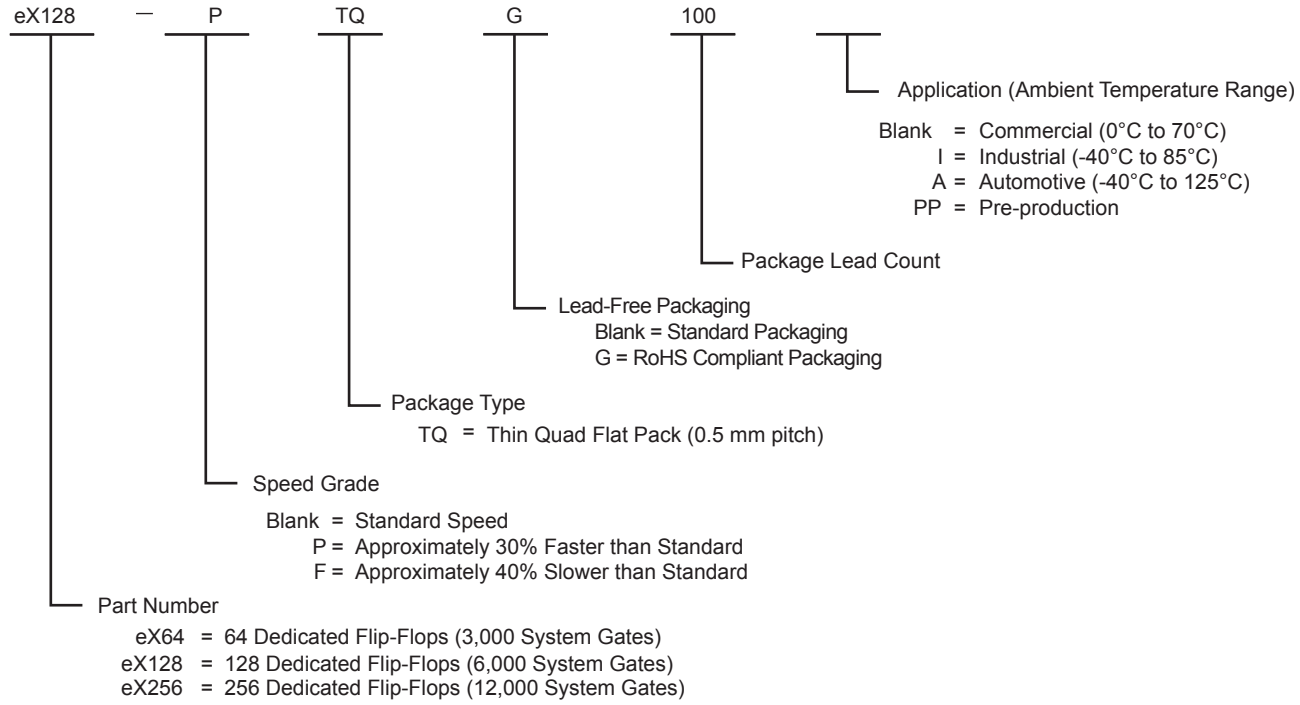
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	128
Total RAM Bits	-
Number of I/O	41
Number of Gates	3000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	64-LQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/ex64-ptq64i

Ordering Information



eX Device Status

eX Devices	Status
eX64	Production
eX128	Production
eX256	Production

Plastic Device Resources

Device	User I/Os (Including Clock Buffers)	
	TQ64	TQ100
eX64	41	56
eX128	46	70
eX256	—	81

Note: TQ = Thin Quad Flat Pack

Temperature Grade Offerings

Device\ Package	TQ64	TQ100
eX64	C, I, A	C, I, A
eX128	C, I, A	C, I, A
eX256	C, I, A	C, I, A

Note: C = Commercial
I = Industrial
A = Automotive

Speed Grade and Temperature Grade Matrix

	–F	Std	–P
C	✓	✓	✓
I		✓	✓
A		✓	

Note: P = Approximately 30% faster than Standard
–F = Approximately 40% slower than Standard
Refer to the eX Automotive Family FPGAs datasheet for details on automotive temperature offerings.

Contact your local Microsemi representative for device availability.

Routing Resources

Clusters and SuperClusters can be connected through the use of two innovative local routing resources called FastConnect and DirectConnect, which enable extremely fast and predictable interconnection of modules within Clusters and SuperClusters (Figure 1-4). This routing architecture also dramatically reduces the number of antifuses required to complete a circuit, ensuring the highest possible performance.

DirectConnect is a horizontal routing resource that provides connections from a C-cell to its neighboring R-cell in a given SuperCluster. DirectConnect uses a hard-wired signal path requiring no programmable interconnection to achieve its fast signal propagation time of less than 0.1 ns (–P speed grade).

FastConnect enables horizontal routing between any two logic modules within a given SuperCluster and vertical routing with the SuperCluster immediately below it. Only one programmable connection is used in a FastConnect path, delivering maximum pin-to-pin propagation of 0.3 ns (–P speed grade).

In addition to DirectConnect and FastConnect, the architecture makes use of two globally oriented routing resources known as segmented routing and high-drive routing. The segmented routing structure of Microsemi provides a variety of track lengths for extremely fast routing between SuperClusters. The exact combination of track lengths and antifuses within each path is chosen by the fully automatic place-and-route software to minimize signal propagation delays.

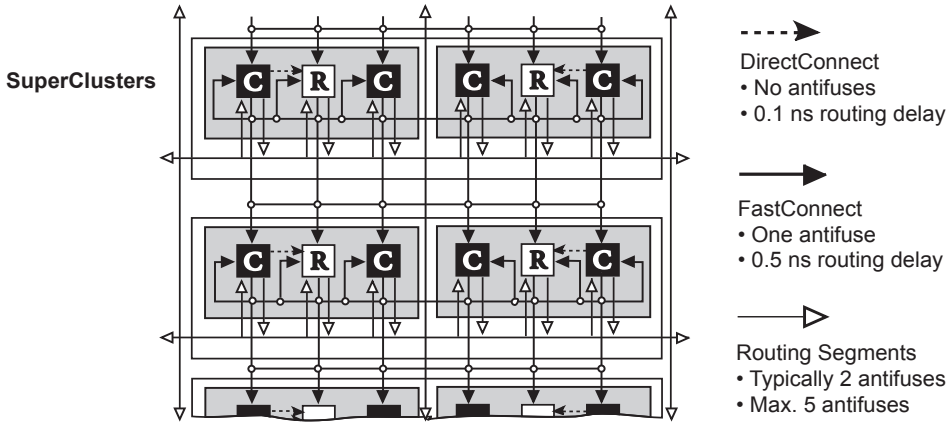


Figure 1-4 • **DirectConnect and FastConnect for SuperClusters**

Clock Resources

eX's high-drive routing structure provides three clock networks. The first clock, called HCLK, is hardwired from the HCLK buffer to the clock select MUX in each R-Cell. HCLK cannot be connected to combinational logic. This provides a fast propagation path for the clock signal, enabling the 3.9 ns clock-to-out (pad-to-pad) performance of the eX devices. The hard-wired clock is tuned to provide a clock skew of less than 0.1 ns worst case. If not used, the HCLK pin must be tied LOW or HIGH and must not be left floating. Figure 1-5 describes the clock circuit used for the constant load HCLK.

HCLK does not function until the fourth clock cycle each time the device is powered up to prevent false output levels due to any possible slow power-on-reset signal and fast start-up clock circuit. To activate HCLK from the first cycle, the TRST pin must be reserved in the Design software and the pin must be tied to GND on the board. (See the "TRST, I/O Boundary Scan Reset Pin" on page 1-32).

The remaining two clocks (CLKA, CLKB) are global routed clock networks that can be sourced from external pins or from internal logic signals (via the CLKINT routed clock buffer) within the eX device. CLKA and CLKB may be connected to sequential cells or to combinational logic. If CLKA or CLKB is sourced from internal logic signals, the external clock pin cannot be used for any other input and must be tied LOW or HIGH and must not float. Figure 1-6 describes the CLKA and CLKB circuit used in eX devices.

Table 1-1 describes the possible connections of the routed clock networks, CLKA and CLKB. Unused clock pins must not be left floating and must be tied to HIGH or LOW.

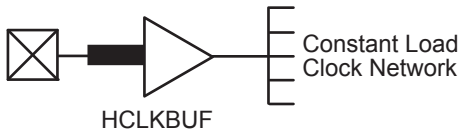


Figure 1-5 • **eX HCLK Clock Pad**

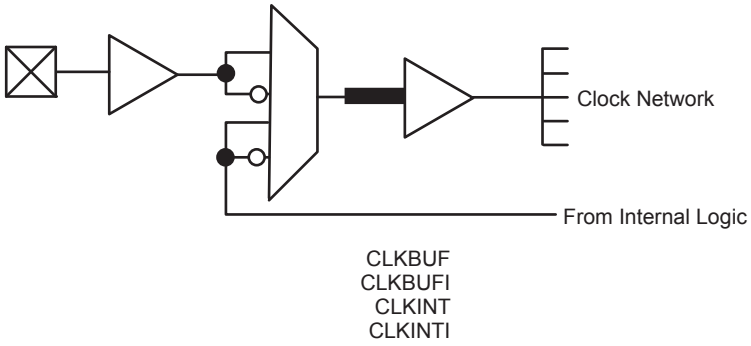


Figure 1-6 • **eX Routed Clock Buffer**

Table 1-1 • **Connections of Routed Clock Networks, CLKA and CLKB**

Module	Pins
C-Cell	A0, A1, B0 and B1
R-Cell	CLKA, CLKB, S0, S1, PSET, and CLR
I/O-Cell	EN

Other Architectural Features

Performance

The combination of architectural features described above enables eX devices to operate with internal clock frequencies exceeding 350 MHz for very fast execution of complex logic functions. The eX family is an optimal platform upon which the functionality previously contained in CPLDs can be integrated. eX devices meet the performance goals of gate arrays, and at the same time, present significant improvements in cost and time to market. Using timing-driven place-and-route tools, designers can achieve highly deterministic device performance.

User Security

Microsemi FuseLock advantage provides the highest level of protection in the FPGA industry against unauthorized modifications. In addition to the inherent strengths of the architecture, special security fuses that are intended to prevent internal probing and overwriting are hidden throughout the fabric of the device. They are located such that they cannot be accessed or bypassed without destroying the rest of the device, making Microsemi antifuse FPGAs highly resistant to both invasive and more subtle noninvasive attacks.

Look for this symbol to ensure your valuable IP is secure. The FuseLock Symbol on the FPGA ensures that the device is safeguarded to cryptographic attacks.

Figure 1-7 • **Fuselock**

For more information, refer to *Implementation of Security in Microsemi Antifuse FPGAs* application note.

I/O Modules

Each I/O on an eX device can be configured as an input, an output, a tristate output, or a bidirectional pin. Even without the inclusion of dedicated I/O registers, these I/Os, in combination with array registers, can achieve clock-to-out (pad-to-pad) timing as fast as 3.9 ns. I/O cells in eX devices do not contain embedded latches or flip-flops and can be inferred directly from HDL code. The device can easily interface with any other device in the system, which in turn enables parallel design of system components and reduces overall design time.

All unused I/Os are configured as tristate outputs by Microsemi's Designer software, for maximum flexibility when designing new boards or migrating existing designs. Each I/O module has an available pull-up or pull-down resistor of approximately 50 kΩ that can configure the I/O in a known state during power-up. Just shortly before V_{CCA} reaches 2.5 V, the resistors are disabled and the I/Os will be controlled by user logic.

To exit the LP mode, the LP pin must be driven LOW for over 200 µs to allow for the charge pumps to power-up and device initialization can begin.

Table 1-3 illustrates the standby current of eX devices in LP mode.

Table 1-3 • **Standby Power of eX Devices in LP Mode Typical Conditions, V_{CCA}, V_{CCI} = 2.5 V, T_J = 25° C**

Product	Low Power Standby Current	Units
eX64	100	µA
eX128	111	µA
eX256	134	µA

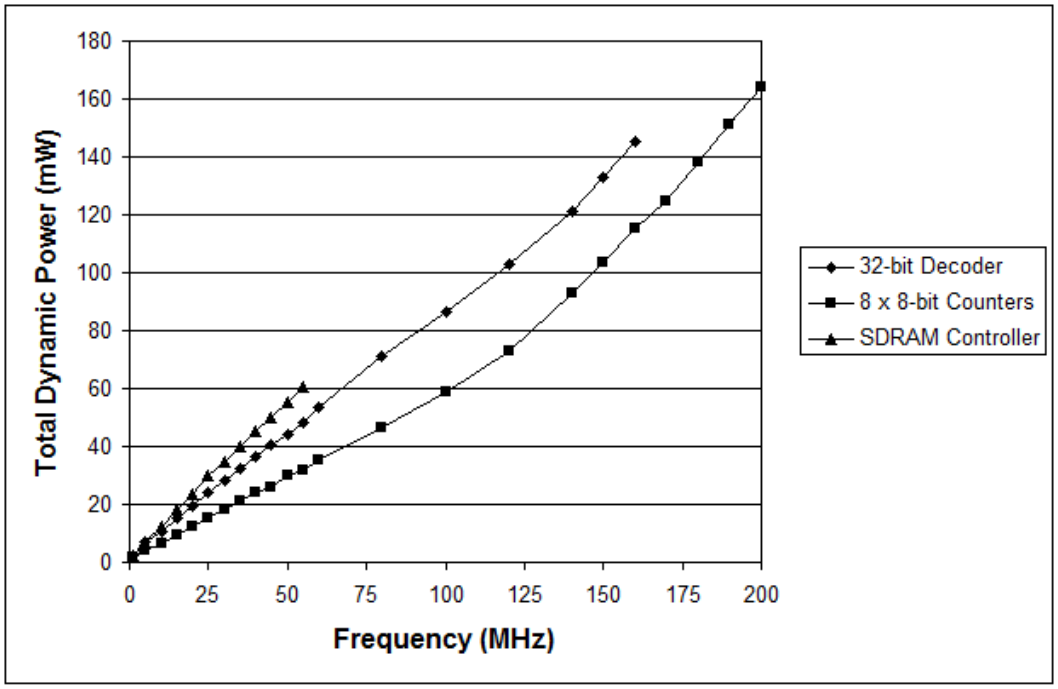


Figure 1-10 • **Total Dynamic Power (mW)**

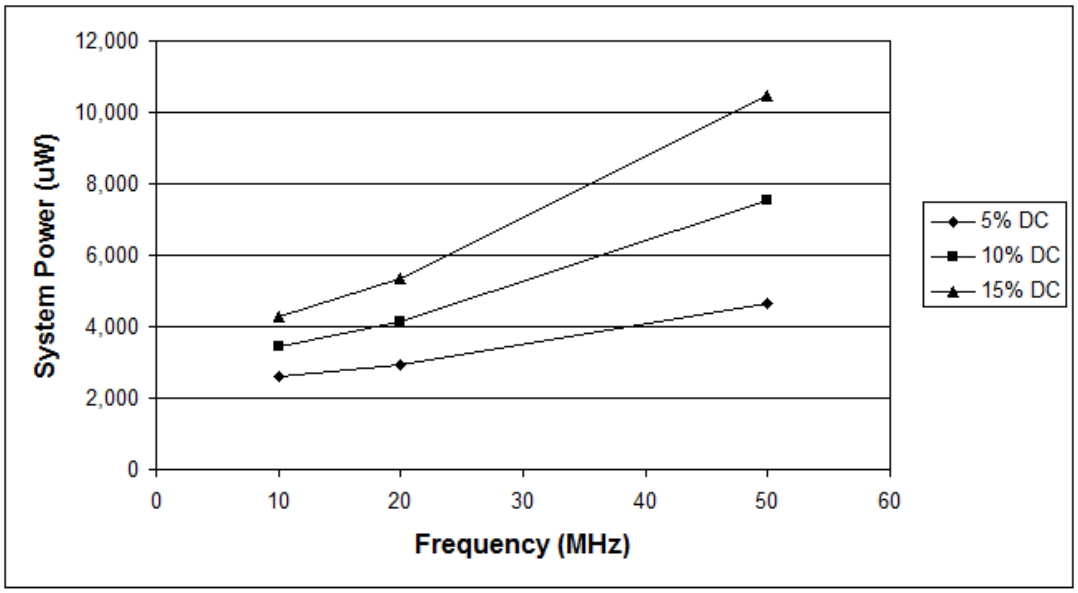


Figure 1-11 • **System Power at 5%, 10%, and 15% Duty Cycle**

Table 1-5 describes the different configuration requirements of BST pins and their functionality in different modes.

Table 1-5 • **Boundary-Scan Pin Configurations and Functions**

Mode	Designer "Reserve JTAG" Selection	TAP Controller State
Dedicated (JTAG)	Checked	Any
Flexible (User I/O)	Unchecked	Test-Logic-Reset
Flexible (JTAG)	Unchecked	Any EXCEPT Test-Logic-Reset

TRST Pin

The TRST pin functions as a dedicated Boundary-Scan Reset pin when the **Reserve JTAG Test Reset** option is selected, as shown in Figure 1-12. An internal pull-up resistor is permanently enabled on the TRST pin in this mode. It is recommended to connect this pin to GND in normal operation to keep the JTAG state controller in the Test-Logic-Reset state. When JTAG is being used, it can be left floating or be driven HIGH.

When the **Reserve JTAG Test Reset** option is not selected, this pin will function as a regular I/O. If unused as an I/O in the design, it will be configured as a tristated output.

JTAG Instructions

Table 1-6 lists the supported instructions with the corresponding IR codes for eX devices.

Table 1-6 • **JTAG Instruction Code**

Instructions (IR4: IR0)	Binary Code
EXTEST	00000
SAMPLE / PRELOAD	00001
INTEST	00010
USERCODE	00011
IDCODE	00100
HIGHZ	01110
CLAMP	01111
Diagnostic	10000
BYPASS	11111
Reserved	All others

Table 1-7 lists the codes returned after executing the IDCODE instruction for eX devices. Note that bit 0 is always “1.” Bits 11-1 are always “02F”, which is Microsemi SoC Products Group's manufacturer code.

Table 1-7 • **IDCODE for eX Devices**

Device	Revision	Bits 31-28	Bits 27-12
eX64	0	8	40B2, 42B2
eX128	0	9	40B0, 42B0
eX256	0	9	40B5, 42B5
eX64	1	A	40B2, 42B2
eX128	1	B	40B0, 42B0
eX256	1	B	40B5, 42B5

Programming

Device programming is supported through Silicon Sculptor series of programmers. In particular, Silicon Sculptor II is a compact, robust, single-site and multi-site device programmer for the PC.

With standalone software, Silicon Sculptor II allows concurrent programming of multiple units from the same PC, ensuring the fastest programming times possible. Each fuse is subsequently verified by Silicon Sculptor II to insure correct programming. In addition, integrity tests ensure that no extra fuses are programmed. Silicon Sculptor II also provides extensive hardware self-testing capability.

The procedure for programming an eX device using Silicon Sculptor II is as follows:

1. Load the *.AFM file
2. Select the device to be programmed
3. Begin programming

When the design is ready to go to production, Microsemi offers device volume-programming services either through distribution partners or via in-house programming from the factory.

For more details on programming eX devices, please refer to the *Programming Antifuse Devices* application note and the *Silicon Sculptor II User's Guide*.

Probing Capabilities

eX devices provide internal probing capability that is accessed with the JTAG pins. The Silicon Explorer II Diagnostic hardware is used to control the TDI, TCK, TMS and TDO pins to select the desired nets for debugging. The user simply assigns the selected internal nets in the Silicon Explorer II software to the PRA/PRB output pins for observation. Probing functionality is activated when the BST pins are in JTAG mode and the TRST pin is driven HIGH or left floating. If the TRST pin is held LOW, the TAP controller will remain in the Test-Logic-Reset state so no probing can be performed. The Silicon Explorer II automatically places the device into JTAG mode, but the user must drive the TRST pin HIGH or allow the internal pull-up resistor to pull TRST HIGH.

When you select the **Reserve Probe Pin** box, as shown in Figure 1-12 on page 1-10, the layout tool reserves the PRA and PRB pins as dedicated outputs for probing. This reserve option is merely a guideline. If the Layout tool requires that the PRA and PRB pins be user I/Os to achieve successful layout, the tool will use these pins for user I/Os. If you assign user I/Os to the PRA and PRB pins and select the **Reserve Probe Pin** option, Designer Layout will override the "Reserve Probe Pin" option and place your user I/Os on those pins.

To allow for probing capabilities, the security fuse must not be programmed. Programming the security fuse will disable the probe circuitry. Table 1-8 on page 1-13 summarizes the possible device configurations for probing once the device leaves the Test-Logic-Reset JTAG state.

Silicon Explorer II Probe

Silicon Explorer II is an integrated hardware and software solution that, in conjunction with Microsemi Designer software tools, allow users to examine any of the internal nets of the device while it is operating in a prototype or a production system. The user can probe into an eX device via the PRA and PRB pins without changing the placement and routing of the design and without using any additional resources. Silicon Explorer II's noninvasive method does not alter timing or loading effects, thus shortening the debug cycle.

Silicon Explorer II does not require re-layout or additional MUXes to bring signals out to an external pin, which is necessary when using programmable logic devices from other suppliers.

Silicon Explorer II samples data at 100 MHz (asynchronous) or 66 MHz (synchronous). Silicon Explorer II attaches to a PC's standard COM port, turning the PC into a fully functional 18-channel logic analyzer. Silicon Explorer II allows designers to complete the design verification process at their desks and reduces verification time from several hours per cycle to a few seconds.

The Silicon Explorer II tool uses the boundary scan ports (TDI, TCK, TMS and TDO) to select the desired nets for verification. The selected internal nets are assigned to the PRA/PRB pins for observation. Figure 1-13 on page 1-13 illustrates the interconnection between Silicon Explorer II and the eX device to perform in-circuit verification.

Designer software is a place-and-route tool and provides a comprehensive suite of backend support tools for FPGA development. The Designer software includes timing-driven place-and-route, and a world-class integrated static timing analyzer and constraints editor. With the Designer software, a user can lock his/her design pins before layout while minimally impacting the results of place-and-route. Additionally, the back-annotation flow is compatible with all the major simulators and the simulation results can be cross-probed with Silicon Explorer II, Microsemi integrated verification and logic analysis tool. Another tool included in the Designer software is the SmartGen core generator, which easily creates popular and commonly used logic functions for implementation into your schematic or HDL design. Microsemi's Designer software is compatible with the most popular FPGA design entry and verification tools from companies such as Mentor Graphics, Synplicity, Synopsys, and Cadence Design Systems. The Designer software is available for both the Windows and UNIX operating systems.

2.5 V LVCMOS2 Electrical Specifications

Symbol	Parameter		Commercial Min.	Commercial Max.	Industrial Min.	Industrial Max.	Units
VOH	VCCI = MIN, VI = VIH or VIL	(IOH = –100 mA)	2.1		2.1		V
	VCCI = MIN, VI = VIH or VIL	(IOH = –1 mA)	2.0		2.0		V
	VCCI = MIN, VI = VIH or VIL	(IOH = –2 mA)	1.7		1.7		V
VOL	VCCI = MIN, VI = VIH or VIL	(IOL = 100 mA)		0.2		0.2	V
	VCCI = MIN, VI = VIH or VIL	(IOL = 1mA)		0.4		0.4	V
	VCCI = MIN,VI = VIH or VIL	(IOL = 2 mA)		0.7		0.7	V
VIL	Input Low Voltage, VOUT ≤ VOL (max.)		–0.3	0.7	-0.3	0.7	V
VIH	Input High Voltage, VOUT ≥ VOH (min.)		1.7	VCCI + 0.3	1.7	VCCI + 0.3	V
IIL/ IIH	Input Leakage Current, VIN = VCCI or GND		–10	10	–10	10	µA
IOZ	3-State Output Leakage Current, VOUT = VCCI or GND		–10	10	–10	10	µA
t_R, $t_{F1,2}$	Input Transition Time			10		10	ns
C_{IO}	I/O Capacitance			10		10	pF
ICC[3,4]	Standby Current			1.0		3.0	mA
IV Curve	Can be derived from the IBIS model at www.microsemi.com/soc/custsup/models/ibis.html.						

Notes:

1. *t_R is the transition time from 0.7 V to 1.7 V.*
2. *t_F is the transition time from 1.7 V to 0.7 V.*
3. *I_{CC} max Commercial –F = 5.0 mA*
4. *$I_{CC} = I_{CCI} + I_{CCA}$*

Power Dissipation

Power consumption for eX devices can be divided into two components: static and dynamic.

Static Power Component

The power due to standby current is typically a small component of the overall power. Typical standby current for eX devices is listed in the Table 1-11 on page 1-16. For example, the typical static power for eX128 at 3.3 V V_{CCI} is:

ICC * VCCA = 795 µA x 2.5 V = 1.99 mW

Dynamic Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. This component is frequency-dependent and a function of the logic and the external I/O. Dynamic power dissipation results from charging internal chip capacitance due to PC board traces and load device inputs. An additional component of the dynamic power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent dynamic power dissipation.

Dynamic power dissipation = CEQ * $VCCA^2$ x F

where:

CEQ = Equivalent capacitance

F = switching frequency

Equivalent capacitance is calculated by measuring ICCA at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency-independent, so the results can be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

CEQ Values for eX Devices

Combinatorial modules (Ceqcm)	1.70 pF
Sequential modules (Ceqsm)	1.70 pF
Input buffers (Ceqi)	1.30 pF
Output buffers (Ceqo)	7.40 pF
Routed array clocks (Ceqcr)	1.05 pF

The variable and fixed capacitance of other device components must also be taken into account when estimating the dynamic power dissipation.

Table 1-12 shows the capacitance of the clock components of eX devices.

***Table 1-12* • Capacitance of Clock Components of eX Devices**

	eX64	eX128	eX256
Dedicated array clock – variable (Ceqhv)	0.85 pF	0.85 pF	0.85 pF
Dedicated array clock – fixed (Ceqhf)	18.00 pF	20.00 pF	25.00 pF
Routed array clock A (r1)	23.00 pF	28.00 pF	35.00 pF
Routed array clock B (r2)	23.00 pF	28.00 pF	35.00 pF

The estimation of the dynamic power dissipation is a piece-wise linear summation of the power dissipation of each component.

$$\text{Dynamic power dissipation} = VCCA^2 * [(m_c * C_{eqcm} * fm_C)_{\text{Comb Modules}} + (m_s * C_{eqsm} * fm_S)_{\text{Seq Modules}} + (n * C_{eqi} * fn)_{\text{Input Buffers}} + (0.5 * (q1 * C_{eqcr} * fq1) + (r1 * fq1))_{RCLKA} + (0.5 * (q2 * C_{eqcr} * fq2) + (r2 * fq2))_{RCLKB} + (0.5 * (s1 * C_{eqhv} * fs1)+(C_{eqhf} * fs1))_{HCLK}] + V_{CCI}^2 * [(p * (C_{eqo} + C_L) * fp)_{\text{Output Buffers}}]$$

where:

m_c = Number of combinatorial cells switching at frequency fm, typically 20% of C-cells
m_s = Number of sequential cells switching at frequency fm, typically 20% of R-cells
n = Number of input buffers switching at frequency fn, typically number of inputs / 4
p = Number of output buffers switching at frequency fp, typically number of outputs / 4
q1 = Number of R-cells driven by routed array clock A
q2 = Number of R-cells driven by routed array clock B
r1 = Fixed capacitance due to routed array clock A
r2 = Fixed capacitance due to routed array clock B
s1 = Number of R-cells driven by dedicated array clock
C_{eqcm} = Equivalent capacitance of combinatorial modules
C_{eqsm} = Equivalent capacitance of sequential modules
C_{eqi} = Equivalent capacitance of input buffers
C_{eqcr} = Equivalent capacitance of routed array clocks
C_{eqhv} = Variable capacitance of dedicated array clock
C_{eqhf} = Fixed capacitance of dedicated array clock
C_{eqo} = Equivalent capacitance of output buffers
C_L = Average output loading capacitance, typically 10 pF
fm_c = Average C-cell switching frequency, typically F/10
fm_s = Average R-cell switching frequency, typically F/10
fn = Average input buffer switching frequency, typically F/5
fp = Average output buffer switching frequency, typically F/5
fq1 = Frequency of routed clock A
fq2 = Frequency of routed clock B
fs1 = Frequency of dedicated array clock

The eX, SX-A and RTSX-S Power Calculator can be used to estimate the total power dissipation (static and dynamic) of eX devices: www.microsemi.com/soc/techdocs/calculators.aspx.

Input Buffer Delays

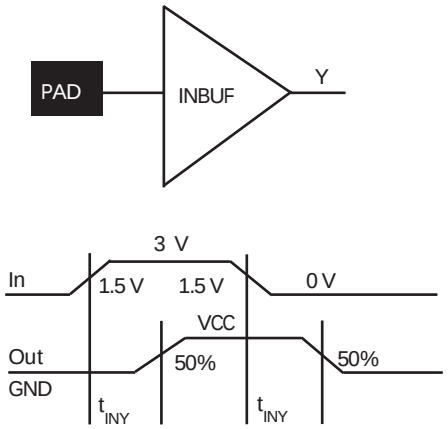


***Table 1-14* • Input Buffer Delays**

C-Cell Delays

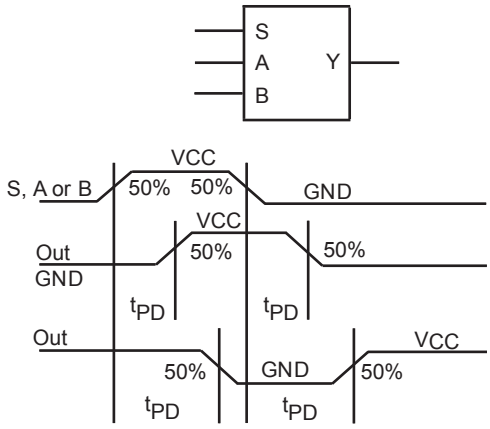


***Table 1-15* • C-Cell Delays**

Cell Timing Characteristics

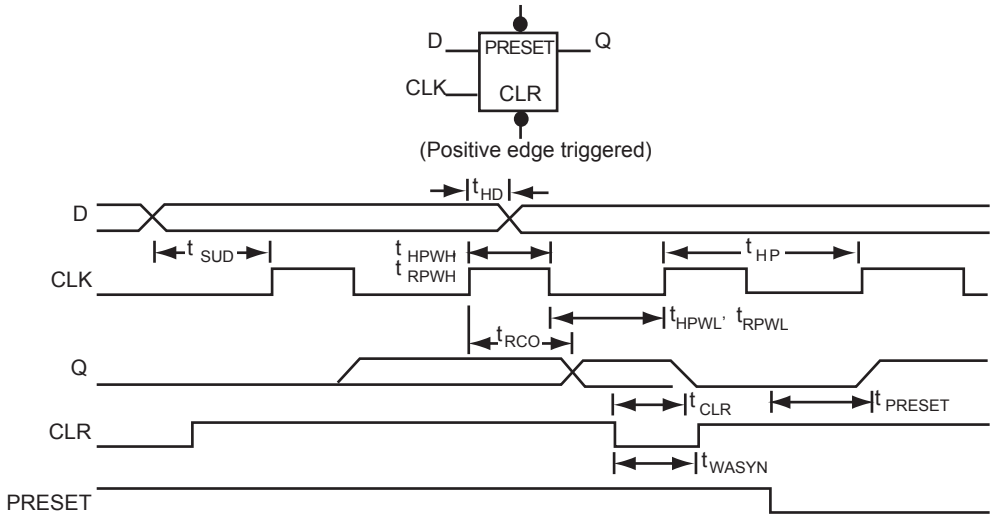


Figure 1-16 • **Flip-Flops**

eX Family Timing Characteristics

***Table 1-17* • eX Family Timing Characteristics**
(Worst-Case Commercial Conditions, VCCA = 2.3 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	**Description**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
C-Cell Propagation Delays[1]								
t_{PD}	Internal Array Module		0.7		1.0		1.4	ns
Predicted Routing Delays[2]								
t_{DC}	FO=1 Routing Delay, DirectConnect		0.1		0.1		0.2	ns
t_{FC}	FO=1 Routing Delay, FastConnect		0.3		0.5		0.7	ns
t_{RD1}	FO=1 Routing Delay		0.3		0.5		0.7	ns
t_{RD2}	FO=2 Routing Delay		0.4		0.6		0.8	ns
t_{RD3}	FO=3 Routing Delay		0.5		0.8		1.1	ns
t_{RD4}	FO=4 Routing Delay		0.7		1.0		1.3	ns
t_{RD8}	FO=8 Routing Delay		1.2		1.7		2.4	ns
t_{RD12}	FO=12 Routing Delay		1.7		2.5		3.5	ns
R-Cell Timing								
t_{RCO}	Sequential Clock-to-Q		0.6		0.9		1.3	ns
t_{CLR}	Asynchronous Clear-to-Q		0.6		0.8		1.2	ns
t_{PRESET}	Asynchronous Preset-to-Q		0.7		0.9		1.3	ns
t_{SUD}	Flip-Flop Data Input Set-Up	0.5		0.7		1.0		ns
t_{HD}	Flip-Flop Data Input Hold	0.0		0.0		0.0		ns
t_{WASYN}	Asynchronous Pulse Width	1.3		1.9		2.6		ns
$t_{RECASYN}$	Asynchronous Recovery Time	0.3		0.5		0.7		ns
t_{HASYN}	Asynchronous Hold Time	0.3		0.5		0.7		ns
2.5 V Input Module Propagation Delays								
t_{INYH}	Input Data Pad-to-Y HIGH		0.6		0.9		1.3	ns
t_{INYL}	Input Data Pad-to-Y LOW		0.8		1.1		1.5	ns
3.3 V Input Module Propagation Delays								
t_{INYH}	Input Data Pad-to-Y HIGH		0.7		1.0		1.4	ns
t_{INYL}	Input Data Pad-to-Y LOW		0.9		1.3		1.8	ns
5.0 V Input Module Propagation Delays								
t_{INYH}	Input Data Pad-to-Y HIGH		0.7		1.0		1.4	ns
t_{INYL}	Input Data Pad-to-Y LOW		0.9		1.3		1.8	ns
Input Module Predicted Routing Delays[2]								
t_{IRD1}	FO=1 Routing Delay		0.3		0.4		0.5	ns
t_{IRD2}	FO=2 Routing Delay		0.4		0.6		0.8	ns
t_{IRD3}	FO=3 Routing Delay		0.5		0.8		1.1	ns
t_{IRD4}	FO=4 Routing Delay		0.7		1.0		1.3	ns
t_{IRD8}	FO=8 Routing Delay		1.2		1.7		2.4	ns
t_{IRD12}	FO=12 Routing Delay		1.7		2.5		3.5	ns

Notes:

1. *For dual-module macros, use t_{PD} + t_{RD1} + t_{PDn}, t_{RCO} + t_{RD1} + t_{PDn} or t_{PD1} + t_{RD1} + t_{SUD}, whichever is appropriate.*
2. *Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance.*

Table 1-18 • **eX Family Timing Characteristics**
(Worst-Case Commercial Conditions VCCA = 2.3 V, VCCI = 4.75 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	**Description**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
Dedicated (Hard-Wired) Array Clock Networks								
t_{HCKH}	Input LOW to HIGH (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t_{HCKL}	Input HIGH to LOW (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t_{HPWH}	Minimum Pulse Width HIGH	1.4		2.0		2.8		ns
t_{HPWL}	Minimum Pulse Width LOW	1.4		2.0		2.8		ns
t_{HCKSW}	Maximum Skew		<0.1		<0.1		<0.1	ns
t_{HP}	Minimum Period	2.8		4.0		5.6		ns
f_{HMAX}	Maximum Frequency		357		250		178	MHz
Routed Array Clock Networks								
t_{RCKH}	Input LOW to HIGH (Light Load) (Pad to R-Cell Input) MAX.		1.1		1.6		2.2	ns
t_{RCKL}	Input HIGH to LOW (Light Load) (Pad to R-Cell Input) MAX.		1.0		1.4		2.0	ns
t_{RCKH}	Input LOW to HIGH (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t_{RCKL}	Input HIGH to LOW (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t_{RCKH}	Input LOW to HIGH (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t_{RCKL}	Input HIGH to LOW (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t_{RPWH}	Min. Pulse Width HIGH	1.5		2.1		3.0		ns
t_{RPWL}	Min. Pulse Width LOW	1.5		2.1		3.0		ns
t_{RCKSW}*	Maximum Skew (Light Load)		0.2		0.3		0.4	ns
t_{RCKSW}*	Maximum Skew (50% Load)		0.1		0.2		0.3	ns
t_{RCKSW}*	Maximum Skew (100% Load)		0.1		0.1		0.2	ns

*Note: *Clock skew improves as the clock network becomes more heavily loaded.*

Revision	Changes	Page
v4.0 (continued)	The "Flexible Mode" section was updated.	1-10
	Table 1-5 •Boundary-Scan Pin Configurations and Functions is new.	1-11
	The "TRST Pin" section was updated.	1-11
	The "Probing Capabilities" section is new.	1-12
	The "Programming" section was updated.	1-12
	The "Probing Capabilities" section was updated.	1-12
	The "Silicon Explorer II Probe" section was updated.	1-12
	The "Design Considerations" section was updated.	1-13
	The "Development Tool Support" section was updated.	1-13
	The "Absolute Maximum Ratings*" section was updated.	1-16
	The "Temperature and Voltage Derating Factors" section was updated.	1-26
	The "TDI, I/O Test Data Input" section was updated.	1-31
	The "TDO, I/O Test Data Output" section was updated.	1-31
	The "TMS Test Mode Select" section was updated.	1-32
	The "TRST, I/O Boundary Scan Reset Pin" section was updated.	1-32
	All VSV pins were changed to VCCA. The change affected the following pins: 64-Pin TQFP – Pin 36 100-Pin TQFP – Pin 57 49-Pin CSP – Pin D5 128-Pin CSP– Pin H11 and Pin J1 for eX256 180-Pin CSP – Pins J12 and K2	
v3.0	The "Recommended Operating Conditions" section has been changed.	1-16
	The "3.3 V LVTTL Electrical Specifications" section has been updated.	1-18
	The "5.0 V TTL Electrical Specifications" section has been updated.	1-18
	The "Total Dynamic Power (mW)" section is new.	1-9
	The "System Power at 5%, 10%, and 15% Duty Cycle" section is new.	1-9
	The "eX Timing Model" section has been updated.	1-22
v2.0.1	The I/O Features table, Table 1-2 on page 1-6, was updated.	1-6
	The table, "Standby Power of eX Devices in LP Mode Typical Conditions, VCCA, VCCI = 2.5 V, TJ = 25° C" section, was updated.	1-7
	"Typical eX Standby Current at 25°C" section is a new table.	1-16
	The table in the section, "Package Thermal Characteristics" section has been updated for the 49-Pin CSP.	1-21
	The "eX Timing Model" section has been updated.	1-22
	The timing numbers found in, "eX Family Timing Characteristics" section have been updated.	1-27
	The V_{SV} pin has been added to the "Pin Description" section.	1-31
	Please see the following pin tables for the V_{SV} pin and an important footnote including the pin: "TQ64", "TQ100", "128-Pin CSP", and "180-Pin CSP".	2-1, 2-3, 2-6, 2-11
	The figure, "TQ64" section has been updated.	2-1

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